

UT3N06

Power MOSFET

N-CHANNEL ENHANCEMENT
MODE POWER MOSFET

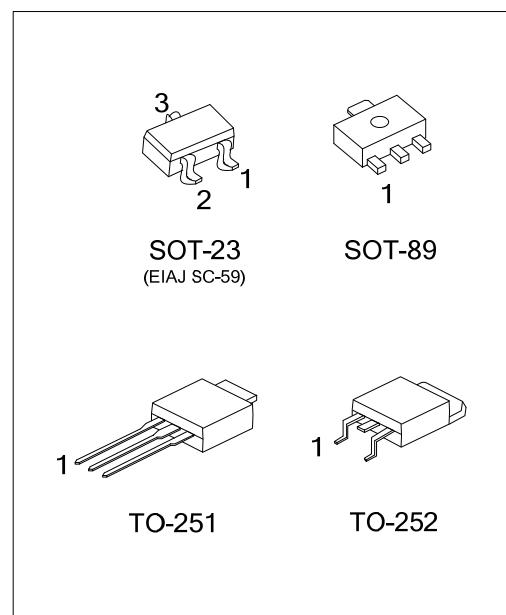
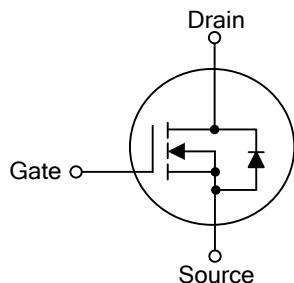
■ DESCRIPTION

The UTC **UT3N06** is an N-channel power MOSFET providing very low on-resistance. It has high efficiency and perfect cost-effectiveness. It can be generally applied in the commercial and industrial fields.

■ FEATURES

- * Simple drive requirement

■ SYMBOL



■ ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | Packing |
|-----------------|---------------|---------|----------------|---|---|-----------|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| - | UT3N06G-AB3-R | SOT-89 | G | D | S | Tape Reel |
| - | UT3N06G-AE3-R | SOT-23 | S | G | D | Tape Reel |
| UT3N06L-TM3-T | UT3N06G-TM3-T | TO-251 | G | D | S | Tube |
| UT3N06L-TN3-R | UT3N06G-TN3-R | TO-252 | G | D | S | Tape Reel |

Note: Pin Assignment: G: Gate D: Drain S: Source

| | |
|-------------------|--|
| UT3N06G-AB3-R | (1) T: Tube, R: Tape Reel (2) AB3: SOT-89, AE3: SOT-23, TM3: TO-251 TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free |
|-------------------|--|

■ MARKING

| SOT-89 | SOT-23 | TO-251 / TO-252 |
|--------|--------|-----------------|
| | | |

■ ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---|------------------|------------|------|
| Drain-Source Voltage | V _{DSS} | 60 | V |
| Gate-Source Voltage | V _{GSS} | ±20 | V |
| Continuous Drain Current (V _{GS} =4.5V, T _A = 25°C) (Note 2) | I _D | 3.0 | A |
| Pulsed Drain Current (Note 3, 4) | I _{DM} | 10 | A |
| | SOT-23 | 0.35 | W |
| Power Dissipation (T _A = 25°C) | P _D | 0.69 | W |
| | SOT-89 | 1.13 | W |
| | TO-251/TO-252 | | |
| Junction Temperature | T _J | +150 | °C |
| Storage Temperature | T _{STG} | -55 ~ +150 | °C |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.
 Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 2. Surface mounted on 1 in² copper pad of FR4 board; 270°C/W when mounted on min. copper pad
 3. Pulse width limited by T_{J(MAX)}
 4. Pulse width ≤300μs, duty cycle≤2%

■ THERMAL DATA

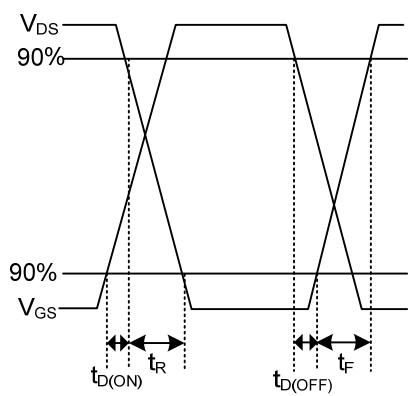
| PARAMETER | SYMBOL | RATING | UNIT |
|---------------------|---------------|--------|------|
| Junction to Ambient | SOT-23 | 350 | °C/W |
| | SOT-89 | 180 | °C/W |
| | TO-251/TO-252 | 110 | °C/W |

■ ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

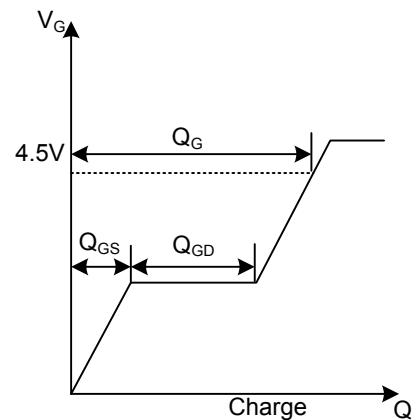
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|---------------------------------------|--|-----|------|------|------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =250μA | 60 | | | V |
| Breakdown Voltage Temperature Coefficient | ΔBV _{DSS} ΔT _J | Reference to 25°C, I _D =1mA | | 0.05 | | V/°C |
| Drain-Source Leakage Current | I _{DSS} | V _{DS} =60V, V _{GS} =0V | | | 10 | μA |
| Gate-Source Leakage Current | I _{GSS} | V _{GS} =±20V | | | ±100 | nA |
| ON CHARACTERISTICS | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | V _{DS} =V _{GS} , I _D =250μA | 1.0 | | 3.0 | V |
| Drain to Source On-state Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =3A | | | 90 | mΩ |
| | | V _{GS} =4.5V, I _D =2A | | | 120 | mΩ |
| DYNAMIC PARAMETERS | | | | | | |
| Input Capacitance | C _{ISS} | V _{DS} =25V, V _{GS} =0V, f =1.0MHz | | 490 | 780 | pF |
| Output Capacitance | C _{OSS} | | | 55 | | pF |
| Reverse Transfer Capacitance | C _{rss} | | | 40 | | pF |
| SWITCHING PARAMETERS | | | | | | |
| Turn-ON Delay Time (Note) | t _{D(ON)} | V _{GS} =10V, V _{DS} =30V, I _D =1A, R _D =30Ω, R _G =3.3Ω | | 6 | | ns |
| Turn-ON Rise Time | t _R | | | 5 | 42 | ns |
| Turn-OFF Delay Time | t _{D(OFF)} | | | 16 | | ns |
| Turn-OFF Fall-Time | t _F | | | 3 | 58 | ns |
| Total Gate Charge (Note) | Q _G | V _{GS} =4.5V, V _{DS} =48V, I _D =3A | | 6 | 10 | nC |
| Gate Source Charge | Q _{GS} | | | 1.6 | | nC |
| Gate Drain Charge | Q _{GD} | | | 3 | | nC |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS | | | | | | |
| Drain-Source Diode Forward Voltage (Note) | V _{SD} | I _S =1.2A, V _{GS} =0V | | | 1.2 | V |
| Reverse Recovery Time | t _{rr} | I _S =3A, V _{GS} =0V, dI/dt=100A/μs | | 25 | | ns |
| Reverse Recovery Charge | Q _{RR} | | | 26 | | nC |

Note: Pulse width ≤300μs, duty cycle≤2%.

■ TEST WAVEFORMS

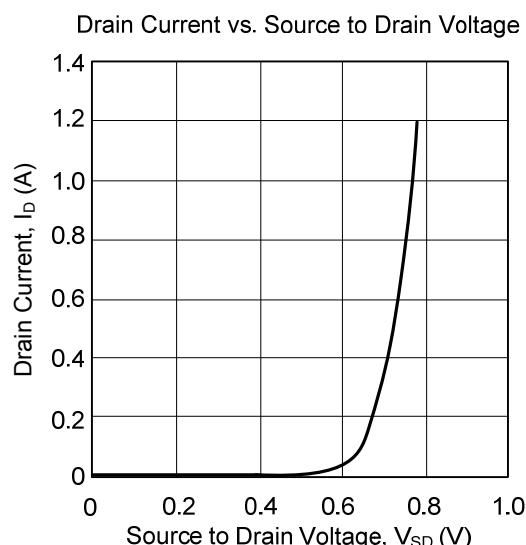
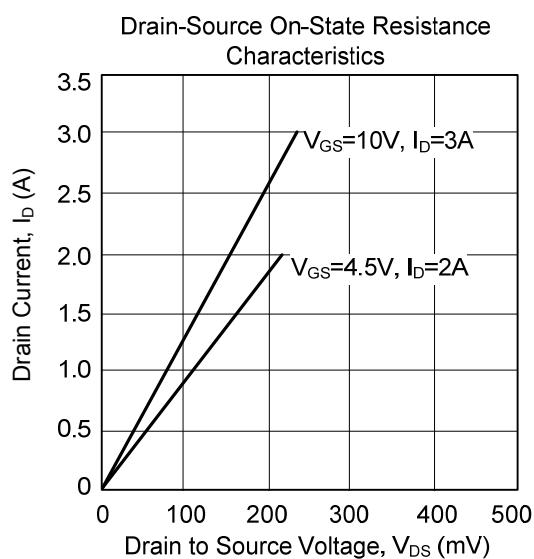
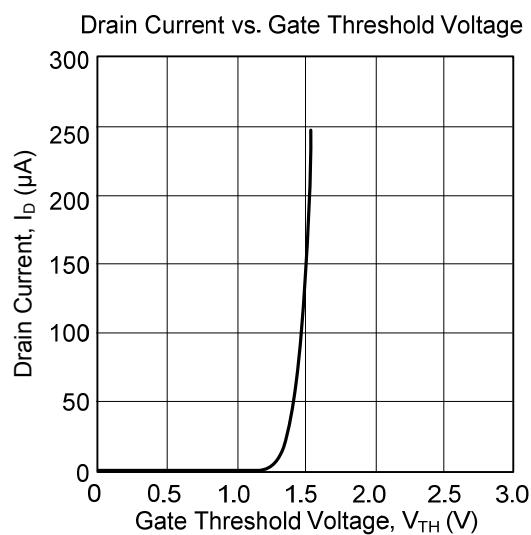
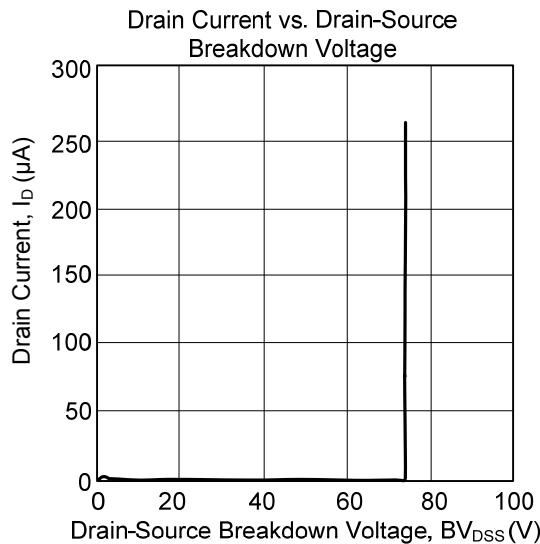


Switching Time Waveform



Gate Charge Waveform

■ TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.